This listing of claims replaces all prior versions of the claims in the Application.

Listing of Claims

Claim 1. (Currently Amended) A method for depositing a seed layer in the manufacture of integrated circuits comprising the step of disposing on a substrate having a non-conductive layer and apertures of ≤ 1 μm a layer comprising one or more conductive polymers to form the seed layer wherein the seed layer has a thickness of from 50 to 1500 angstroms wherein the one or more conductive polymers are selected from the group consisting of polyacetylenes, polyanilines, polypyrroles, polythiophenes and graphite.

Claim 2. (Previously Presented) The method of claim 1 wherein the non-conductive layer is selected from a dielectric layer and a barrier layer.

Claim 3. (Previously Presented) The method of claim 2 wherein the dielectric layer comprises one or more of silicon dioxide, fluorinated silicon dioxide, organopolysilica materials, and organic dielectric materials.

Claim 4. (Previously Presented) The method of claim 2 wherein the barrier layer comprises tantalum, tantalum nitride, titanium, titanium nitride, tungsten, tungsten nitride, molybdenum, molybdenum nitride, cobalt or cobalt nitride.

Claim 5. (Canceled)

Claim 6. (Previously Presented) The method of claim 1 wherein the one or more conductive polymers are substituted.

Claim 7. (Previously Presented) The method of claim 1 wherein the substrate has apertures less than or equal to 0.5 μm.

Claims 8-26 (Canceled)

Claim 27. (Currently Amended) A method of enhancing a seed layer used in the manufacture of integrated circuits comprising the step of: contacting a substrate having a discontinuous seed layer disposed on a non-conductive layer with one or more conductive polymers to provide a substantially continuous seed layer having a thickness of from 50 to 1500 angstroms wherein the substrate comprises apertures of ≤ 1 μm and wherein the one or more

conductive polymers are selected from the group consisting of polyacetylenes, polyanilines, polypyrroles, polythiophenes and graphite.

Claim 28. (Previously Presented) The method of claim 27 wherein the non-conductive layer is selected from a dielectric layer and a barrier layer.

Claim 29. (Previously Presented) The method of claim 28 wherein the dielectric layer comprises one or more of silicon dioxide, fluorinated silicon dioxide, organopolysilica materials, and organic dielectric materials.

Claim 30. (Previously Presented) The method of claim 28 wherein the barrier layer comprises tantalum, tantalum nitride, titanium, titanium nitride, tungsten, tungsten nitride, molybdenum, molybdenum nitride, cobalt or cobalt nitride.

Claim 31. (Canceled)

Claim 32. (Previously Presented) The method of claim 31 wherein the one or more conductive polymers are substituted.

Claim 33. (Previously Presented) The method of claim 27 wherein the substrate has apertures less than or equal to 0.5 μm.

Claim 34. (Canceled)